IMVP7.0 Compatible Synchronous Buck MOSFET Driver

The NCP81051 is a high performance dual MOSFET gate driver optimized to drive the gates of both high-side and low-side power MOSFETs in a synchronous buck converter. It can drive up to 3 nF load with a 25 ns propagation delay and 20 ns transition time.

Adaptive anti-cross-conduction and power saving operation circuit can provide a low switching loss and high efficiency solution for notebook systems.

The UVLO function guarantees the outputs are low when the supply voltage is low.

Features

- Faster Rise and Fall Times
- Adaptive Anti-Cross-Conduction Circuit
- Zero Cross Detection function
- Output Disable Control Turns Off Both MOSFETs
- Undervoltage Lockout
- Power Saving Operation Under Light Load Conditions
- Direct Interface to NCP6131 and Other Compatible PWM Controllers
- Thermally Enhanced Package
- These Devices are Pb-Free and are RoHS Compliant*

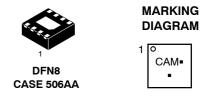
Typical Applications

• Power Management Solutions for Notebook systems



ON Semiconductor®

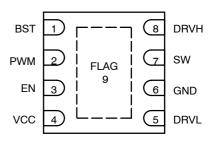
http://onsemi.com





(Note: Microdot may be in either location)





ORDERING INFORMATION

Device	Package	Shipping [†]
NCP81051MNTBG	DFN8 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

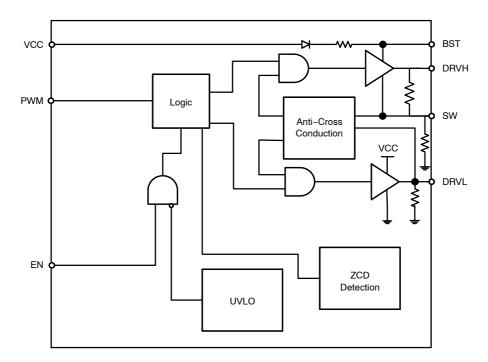


Figure 1. Block Diagram

PIN DESCRIPTIONS

Pin No.	Symbol	Description
1	BST	Floating bootstrap supply pin for high side gate driver. Connect the bootstrap capacitor between this pin and the SW pin.
2	PWM	Control input. The PWM signal has three distinctive states: Low = Low Side FET Enabled, Mid = Diode Emulation Enabled, High = High Side FET Enabled.
3	EN	Logic input. A logic high to enable the part and a logic low to disable the part. Three states logic input: EN = High to enable the gate driver; EN = Low to disable the driver; EN = Mid to go into diode mode (both high and low side gate drive signals are low)
4	VCC	Power supply input. Connect a bypass capacitor (0.1 μ F) from this pin to ground.
5	DRVL	Low side gate drive output. Connect to the gate of low side MOSFET.
6	GND	Bias and reference ground. All signals are referenced to this node.
7	SW	Switch node. Connect this pin to the source of the high side MOSFET and drain of the low side MOSFET.
8	DRVH	High side gate drive output. Connect to the gate of high side MOSFET.
9	FLAG	Thermal flag. There is no electrical connection to the IC. Connect to ground plane.

APPLICATION CIRCUIT

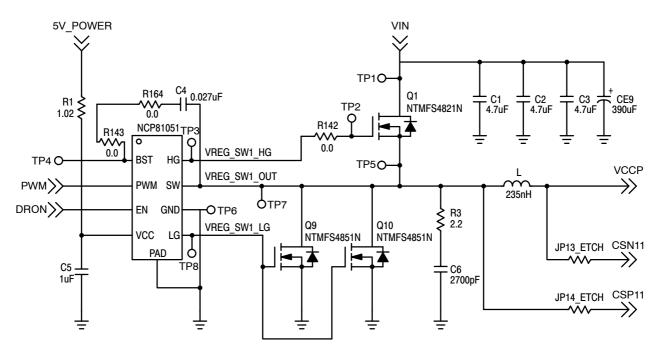


Figure 2. Application Circuit

ABSOLUTE MAXIMUM RATINGS

ELECTRICAL INFORMATION

Symbol	Pin Name	V _{MAX}	V _{MIN}
V _{CC}	Main Supply Voltage Input	6.5 V	–0.3 V
BST	Bootstrap Supply Voltage	35 V wrt/ GND 40 V ≤ 50 ns wrt/ GND 6.5 V wrt/ SW	–0.3 V wrt/SW
SW	Switching Node (Bootstrap Supply Return)	35 V 40 V ≤ 50 ns	_5 V _10 V (200 ns)
DRVH	High Side Driver Output	BST + 0.3 V	–0.3 V wrt/SW –2 V (< 200 ns) wrt/SW
DRVL	Low Side Driver Output	V _{CC} + 0.3 V	–0.3 V DC –5 V (< 200 ns)
PWM	DRVH and DRVL Control Input	6.5 V	–0.3 V
EN	Enable Pin	6.5 V	–0.3 V
GND	Ground	0 V	0 V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability. *All signals referenced to AGND unless noted otherwise.

THERMAL INFORMATION

Symbol	Parameter	Value	Unit
$R_{ heta JA}$	Thermal Characteristic QFN Package (Note 1)	119	°C/W
TJ	Operating Junction Temperature Range (Note 2)	0 to 150	°C
T _A	Operating Ambient Temperature Range	-40 to +100	°C
T _{STG}	Maximum Storage Temperature Range	–55 to +150	°C
MSL	Moisture Sensitivity Level – QFN Package	1	

*The maximum package power dissipation must be observed.

1. 1 in² Cu, 1 oz. thickness.
 2. JESD 51-7 (1S2P Direct-Attach Method) with 1 LFM.

NCP81051 ELECTRICAL CHARACTERISTICS ($-40^{\circ}C < T_A < +100^{\circ}C$; 4.5 V < V_{CC} < 5.5 V, 4.5 V < BST–SWN < 5.5 V, 4.5 V < BST < 30 V, 0 V < SWN < 21 V, unless otherwise noted)

Parameter	Test Conditions	Min	Тур	Max	Unit
SUPPLY VOLTAGE	•	•		<u>.</u>	
VCC Operation Voltage		4.5		5.5	V
UNDERVOLTAGE LOCKOUT			-		
VCC Start Threshold		3.8	4.35	4.5	V
VCC UVLO Hysteresis		150	200	250	mV
SUPPLY CURRENT					
Shutdown Mode	I _{CC} + I _{BST} , EN = GND		15	30	μA
Normal Mode	I_{CC} + I_{BST} , EN = 5 V, PWM = OSC		5.0		mA
Standby Current	I_{CC} + I_{BST} , EN = HIGH, PWM = LOW, No loading on DRVH & DRVL		0.9		mA
Standby Current	I _{CC} + I _{BST} , EN = HIGH, PWM = HIGH, No loading on DRVH & DRVL		1.1		mA
BOOTSTRAP DIODE			-		
Forward Voltage	V_{CC} = 5 V, forward bias current = 2 mA	0.1	0.4	0.6	V
PWM INPUT			-		
PWM Input High		3.4			V
PWM Mid-State		1.3		2.7	V
PWM Input Low				0.7	V
ZCD Blanking Timer			350		ns
HIGH SIDE DRIVER					
Output Impedance, Sourcing Current	$V_{BST} - V_{SW} = 5 V$		0.9	2.0	Ω
Output Impedance, Sinking Current	$V_{BST} - V_{SW} = 5 V$		0.7	2.0	Ω
DRVH Rise Time trdRvh	V_{CC} = 5 V, 3 nF load, V_{BST} – V_{SW} = 5 V		16	25	ns
DRVH Fall Time tfdrvh	V_{CC} = 5 V, 3 nF load, $V_{BST}V_{SW}$ =5 V		11	18	ns
DRVH Turn-Off Propagation Delay tpdlDRVH	C _{LOAD} = 3 nF	10		30	ns
DRVH Turn-On Propagation Delay tpdhDRVH	C _{LOAD} = 3 nF	15		45	ns
SW Pulldown Resistance	SW to PGND		45		kΩ
DRVH Pulldown Resistance	DRVH to SW, BST-SW = 0 V		45		kΩ
LOW SIDE DRIVER	-				
Output Impedance, Sourcing Current			0.9	2.0	Ω
Output Impedance, Sinking Current			0.4	1.0	Ω
DRVL Rise Time trDRVL	C _{LOAD} = 3 nF		16	25	ns
DRVL Fall Time tfDRVL	C _{LOAD} = 3 nF		11	15	ns
DRVL Turn-Off Propagation Delay tpdlDRVL	C _{LOAD} = 3 nF	10		30	ns
DRVL Turn-On Propagation Delay tpdhDRVL	C _{LOAD} = 3 nF	5.0		25	ns
DRVL Pulldown Resistance	DRVL to PGND, V _{CC} = PGND		45		kΩ

NCP81051 ELECTRICAL CHARACTERISTICS ($-40^{\circ}C < T_A < +100^{\circ}C$; 4.5 V < V_{CC} < 5.5 V, 4.5 V < BST–SWN < 5.5 V, 4.5 V < BST < 30 V, 0 V < SWN < 21 V, unless otherwise noted)

Parameter	Test Conditions	Min	Тур	Max	Unit
EN INPUT					
Input Voltage High		3.3			V
Input Voltage Mid		1.35		1.8	V
Input Voltage Low				0.6	V
Input bias current		-1.0		1.0	μA
Propagation Delay Time			20	40	ns
SW NODE					
SW Node Leakage Current				20	μA
Zero Cross Detection Threshold Voltage			-6.0		mV

Table 1. DECODER TRUTH TABLE

Input	ZCD	DRVL	DRVH
PWM High (Enable High)	ZCD Reset	Low	High
PWM Mid (Enable High)	Positive Current Through the Inductor	High	Low
PWM Mid (Enable High)	Zero Current Through the Inductor	Low	Low
PWM Low (Enable High)	ZCD Reset	High	Low
Enable at Mid	Х	Low	Low

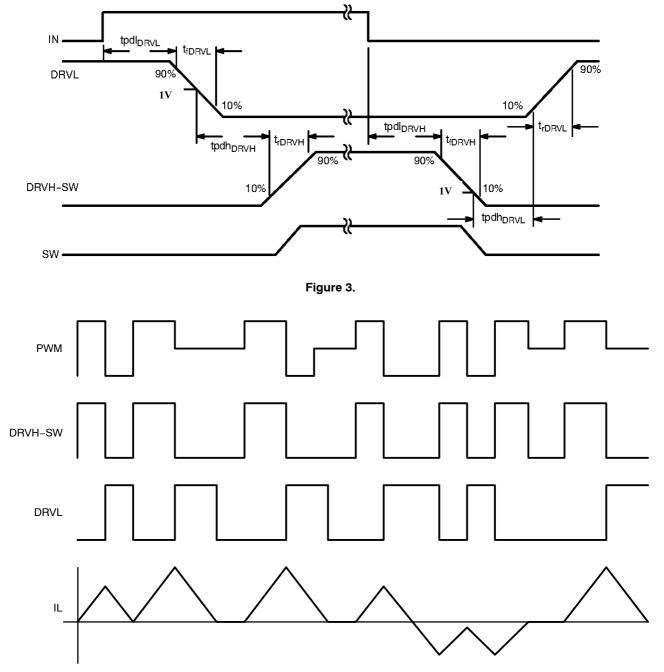


Figure 4. Timing Diagram

APPLICATION INFORMATION

The NCP81051 gate driver is a single phase MOSFET driver designed for driving N-channel MOSFETs in a synchronous buck converter topology. The NCP81051 is designed to work with ON Semiconductor's NCP6131 multi-phase controller. This gate driver is optimized for notebook applications.

Undervoltage Lockout

DRVH and DRVL are held low until VCC reaches 4.5 V during startup. The PWM signal will control the gate status when VCC threshold is exceeded.

Three-State EN Signal

When EN is set to the mid state, both DRVH and DRVL are set low, to force diode mode operation.

PWM Input and Zero Cross Detect (ZCD)

The PWM input, along with EN and ZCD, control the state of DRVH and DRVL.

When PWM is set high, DRVH will be set high after the adaptive non-overlap delay. When PWM is set low, DRVL will be set high after the adaptive non-overlap delay.

When PWM is set to the mid state, DRVH will be set low, and after the adaptive non-overlap delay, DRVL will be set high. DRVL remains high during the ZCD blanking time. When the timer has expired, the SW pin will be monitored for zero cross detection. After the detection, DRVL will be set low.

Adaptive Non-overlap

Adaptive dead time control is used to avoid shoot-through damage of the power MOSFETs. When the PWM signal pulls high, DRVL will be set low and the driver will monitor the gate voltage of the low side MOSFET. When the DRVL voltage falls below the gate threshold, DRVH will be set to high after the tpdhDRVH delay. When PWM is set low, the driver will monitor the gate voltage of the high side MOSFET. When the DRVH–SWN voltage falls below the top gate drive threshold, DRVL will be set to high after the tpdhDRVL delay.

Layout Guidelines

The layout for a DC–DC converter is very important. The bootstrap and VCC bypass capacitors should be placed close to the driver IC.

Connect the GND pin to a local ground plane. The ground plane can provide a good return path for gate drives and reduce the ground noise. The thermal slug should be tied to the ground plane for good heat dissipation. To minimize the ground loop for the low side MOSFET, the driver GND pin should be close to the low-side MOSFET source pin. The gate drive trace should be routed to minimize its length. The minimum width is 20 mils.

Gate Driver Power Loss Calculation

The gate driver power loss consists of the gate drive loss and quiescent power loss.

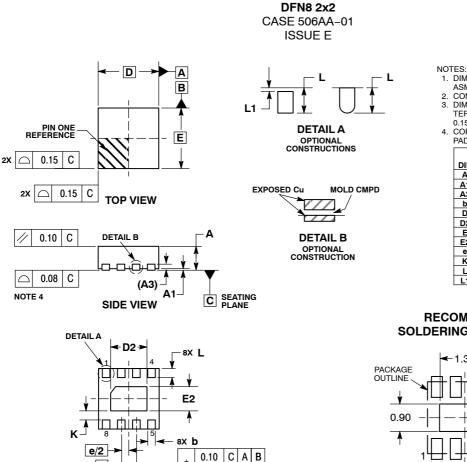
The equation below can be used to calculate the power dissipation of the gate driver. QGMF is the total gate charge for each main MOSFET and QGSF is the total gate charge for each synchronous MOSFET.

 $P_{DRV} =$

$$\left[\frac{f_{SW}}{2 \times n} \times \left(n_{MF} \times Q_{GMF} + n_{SF} \times Q_{GSF}\right) + I_{CC}\right] \times V_{CC}$$
(eq. 1)

Also shown is the standby dissipation factor (ICC x VCC) of the driver.

PACKAGE DIMENSIONS



 \oplus

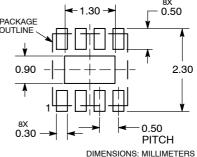
0.05 C NOTE 3

NOTES: 1. DIMENSIONING AND TOLERANCING PER

- ASME Y14.5M, 1994 . 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.80	1.00		
A1	0.00	0.05		
A3	0.20 REF			
b	0.20	0.30		
D	2.00 BSC			
D2	1.10	1.30		
E	2.00	BSC		
E2	0.70	0.90		
е	0.50 BSC			
К	0.30 REF			
L	0.25	0.35		
L1		0.10		

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and use registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use persons, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death agasociated with such unintended or unauthorized to copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

e

BOTTOM VIEW

N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Gate Drivers category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

 89076GBEST
 00053P0231
 56956
 57.404.7355.5
 LT4936
 57.904.0755.0
 5882900001
 00600P0005
 00-9050-LRPP
 00-9090-RDPP

 5951900000
 01-1003W-10/32-15
 0131700000
 00-2240
 LTP70N06
 LVP640
 5J0-1000LG-SIL
 LY1D-2-5S-AC120
 LY2-US-AC240
 LY3

 UA-DC24
 00576P0020
 00600P0010
 LZN4-UA-DC12
 LZNQ2M-US-DC5
 LZNQ2-US-DC12
 LZP40N10
 00-8196-RDPP
 00-8274-RDPP

 00-8275-RDNP
 00-8722-RDPP
 00-8728-WHPP
 00-8869-RDPP
 00-9051-RDPP
 00-9091-LRPP
 00-9291-RDPP
 0207100000
 0207400000

 01312
 0134220000
 60713816
 M15730061
 61161-90
 61278-0020
 6131-204-23149P
 6131-205-17149P
 6131-209-15149P
 6131-218-17149P

 6131-220-21149P
 6131-260-2358P
 6131-265-11149P
 6131-205-17149P
 6131-209-15149P
 6131-218-17149P